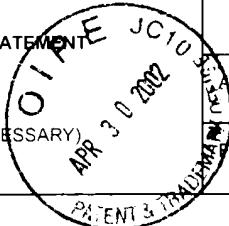


FORM PTO-1449	U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMEX 320A	APPLICATION NO. 10/074,722
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Pomarede et al.	
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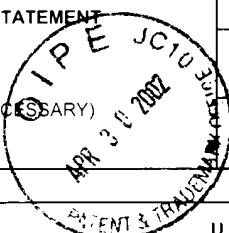


U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
KP	3,900,597	8/19/75	Chruma et al.			
KP	4,217,374	8/12/80	Ovshinsky et al.			
KP	4,237,150	12/2/80	Wiesmann			
KP	4,363,828	12/14/82	Brodsky et al.			
KP	4,379,020	4/5/83	Glaeser et al.			
KP	4,444,812	4/24/84	Gutsche			
KP	4,495,218	1/22/85	Azuma et al.			
KP	4,585,671	4/29/86	Kitagawa et al.			
KP	4,592,933	6/3/86	Meyerson et al.			
KP	4,634,605	1/6/87	Wiesmann			
KP	4,684,542	8/4/87	Jasinski et al.			
KP	4,745,083	5/17/88	Inoue et al.			
KP	4,871,416	10/3/89	Fukuda			
KP	4,963,506	10/16/90	Liaw et al.			
KP	5,037,666	8/6/91	Mori			
KP	5,082,696	1/21/92	Sharp			
KP	5,080,933	1/14/92	Grupen-Shemansky et al.			
KP	5,112,773	5/12/92	Tuttle			
KP	5,198,387	3/30/93	Tang			
KP	5,227,329	7/13/93	Kobayashi et al.			
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KP	5,324,684	6/28/94	Kermani et al.			
KP	5,607,511	3/4/97	Meyerson			
KP	5,607,724	3/4/97	Beinglass et al.			
KP	5,614,257	3/25/97	Beinglass et al.			

EXAMINER	Ron Pomarede	DATE CONSIDERED	2-3-03
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
RP	6,648,293	7/15/97	Hayama et al.			
RP	5,656,531	8/12/97	Thakur et al.			
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RP	5,789,030	8/4/98	Rolfson			
RP	5,837,580	11/17/98	Thakur et al.			
RP	5,863,598	1/26/99	Venkatesan et al.			
RP	5,874,129	2/23/99	Beinglass et al.			
RP	5,876,797	3/2/99	Beinglass et al.			
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RP	5,893,949	4/13/99	King et al.			
RP	5,930,106	7/27/99	DeBoer et al.			
RP	5,998,289	12/7/99	Sagnes			
RP	6,027,705	2/22/00	Kitsuno et al.			11/30/98
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RP	6,083,810	7/4/00	Obeng et al.			12/5/96
RP	6,197,694 B1	3/6/01	Beinglass			7/31/96

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
RP	54-4066	1/12/79	Japan				✓
RP	57209810 A	12/23/82	Japan			Abstract	
RP	59078918 A	5/8/84	Japan			Abstract	
RP	59078919 A	5/8/84	Japan			Abstract	
RP	60043485 A	3/8/85	Japan			✓	

EXAMINER	for Pomarede	DATE CONSIDERED	2-10-03
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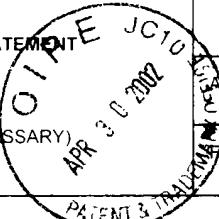
FORM PTO-1449	U S DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMEX 320A	APPLICATION NO 10/074,722
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		JC 10 APR 30 2002 APR 30 2002 PATENT & TRADEMARK OFFICE	
(USE SEVERAL SHEETS IF NECESSARY)		APPLICANT C. Pomarede et al.	
		MAILING DATE February 11, 2002	GROUP Unknown

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
RP	61153277 A	7/11/86	Japan			Abstract	
RP	62076612 A	4/8/87	Japan			Abstract	
RP	63003414 A	1/8/88	Japan			Abstract	
RP	63003463 A	1/8/88	Japan			Abstract	
RP	01217956 A	8/31/89	Japan			Abstract	
RP	01268064 A	10/25/89	Japan			Abstract	
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RP	03187215 A	8/15/91	Japan			✓	
RP	03292741 A	12/24/91	Japan			Abstract	
RP	04323834 A	11/13/92	Japan			Abstract	
RP	05021378 A	1/29/93	Japan			Abstract	
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EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
RP	Angermeier et al., "Initial growth processes in the epitaxy of Ge with GeH ₄ on oxidized Si substrates," <i>J. Electrochem. Soc.</i> , Vol. 144, No. 2, February 1997, pp. 694-697
RP	Bensahel et al., "Industrial single wafer processing of <i>in-situ</i> doped polycrystalline Si and Si _{1-x} Ge _x ," <i>Solid State Technology</i> , March 1998, pp. S5-S10.
RP	Bloem, J., "High chemical vapour deposition rates of epitaxial silicon layers," <i>Journal of Crystal Growth</i> , Vol. 18, (1973), pp. 70-76
RP	Bodnar et al., "Single-wafer Si and SiGe processes for advanced ULSI technologies," <i>Thin Solid Films</i> , Vol. 294, (1997), pp. 11-14.
RP	Rossi, Ronald C., "Low pressure chemical vapor deposition," <i>Handbook of Thin-Film Deposition Processes and Techniques</i> , pp. 80-81
RP	Caymax, et al., "UHV-VLPCVD heteroepitaxial growth of thin SiGe-layers on Si-substrates: Influence of pressure on kinetics and on surface-morphology," <i>Solid State Phenomena</i> , Vol. 32-33, (1993), pp. 361-372
RP	Claassen et al., "Deposition of silicon from silane in a low-pressure hot-wall system," <i>Journal of Crystal Growth</i> , Vol. 57, No. 2, (1982), pp. 259-266
RP	Edwards et al., "Diffusion of Ge along grain boundaries during oxidation of polycrystalline silicon-germanium films," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 319, (1994), pp. 183-188.

EXAMINER <i>Tom Pomarede</i>	DATE CONSIDERED <i>2-10-03</i>
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Pomarede et al.	
(USE SEVERAL SHEETS IF NECESSARY)		FILED DATE February 11, 2002	GROUP Unknown



EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
RP	Edwards et al., "Dopant implantation and activation in polycrystalline-SiGe," <i>Mat. Res. Soc. Meeting – Sym. II</i> , Spring 1994, 6 pages.
RP	Eversteyn et al., "Influence of AsH ₃ , PH ₃ , and B ₂ H ₆ on the growth rate and resistivity of polycrystalline silicon films deposited from a SiH ₄ -H ₂ mixture," <i>Growth Rate and Resistivity of Si Films</i> , Vol. 120, No. 1, January 1973, pp. 106-110.
RP	Hernandez et al., "Evidence of interdiffusion effect in stacked polycrystalline SiGe/Si layers for CMOS gate application," <i>Mat. Res. Soc. Meeting</i> , (19_8), 6 pages.
RP	Kamins et al., "Kinetics of silicon-germanium deposition by atmospheric-pressure chemical vapor deposition," <i>Appl. Phys. Lett.</i> , Vol. 59, No. 2, July 8, 1991, pp. 178-180.
RP	King et al., "A polycrystalline Si _{1-x} Ge _x -gate CMOS technology," <i>IEEE</i> , Vol. 253, (1990), pp. 10.4.1-10.4.4.
RP	Li et al., "Rapid thermal chemical vapor deposition of polycrystalline silicon-germanium films on SiO ₂ and their properties," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol 403, (1996), pp. 333-338.
RP	Lin et al., "Effects of SiH ₄ , GeH ₄ , and B ₂ H ₆ on the nucleation and deposition of polycrystalline Si _{1-x} Ge _x films," <i>J. Electrochem. Soc.</i> , Vol. 141, No. 9, September 1994, pp. 2559-2563.
RP	Morosanu, C E., "Thin films by chemical vapour deposition," <i>Thin Films Science and Technology</i> , 7, pp. 48.
RP	Öztürk et al., "Rapid thermal chemical vapor deposition of germanium on silicon and silicon dioxide and new applications of Ge in ULSI technologies," <i>Journal of Electronic Materials</i> , Vol. 19, No. 10, (1990), pp. 1129-1134.
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EXAMINER	<i>Rm Pomarede</i>	DATE CONSIDERED	<i>2-3-03</i>
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